

UHF power transistor

BLV99

Description:

NPN silicon planar epitaxial transistor encapsulated in a 4-lead SOT172D envelope with a ceramic cap. It is designed primarily for use as a driver stage in base stations in the 900 MHz communications band. All leads are isolated from the mounting base.

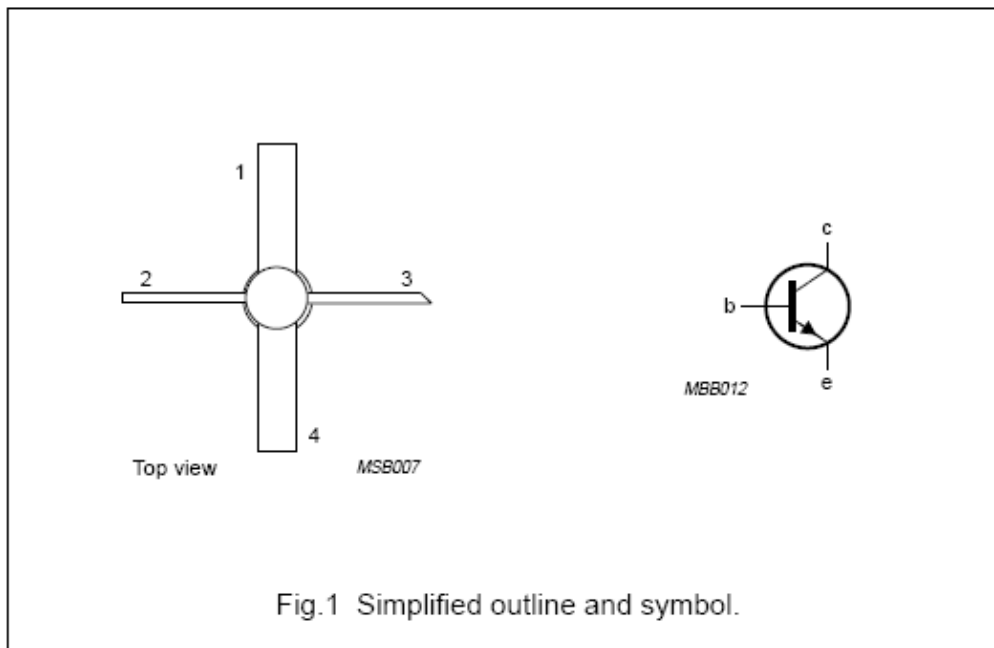
Features:

- * Emitter-ballasting resistors for an optimum temperature profile
- * Gold metallization ensures excellent reliability.

Data:

MODE OF OPERATION	f (MHz)	V _{CE} (V)	P _L (W)	G _p (dB)	η _c (%)
c.w. narrow band	900	24	2	> 8	> 55

Drawings:



PIN	DESCRIPTION
1	emitter
2	base
3	collector
4	emitter